TEXAS INSTRUMENTS
SN74HCS138
JAJSKL6B – OCTOBER 2020 – REVISED MAY 2021

SN74HCS138 3 - 8 ライン・デコーダ / デマルチプレクサ、シュミット・トリガ入力付き

1 特長

- 広い動作電圧範囲:2V～6V
- シュミット・トリガ入力により低速の入力信号またはノイズの多い入力信号に対応
- 低い消費電力
  - I_{CC}:100nA (標準値)
  - 入力リーク電流:±100nA (標準値)
- 6V で±7.8mA の出力駆動能力
- 拡張周囲温度範囲:–40℃～+125℃、T_A

2 アプリケーション

- データ・バスを共有するメモリ・デバイスの選択
- チップ・セレクト・アプリケーションの出力の必要数の低減
- データの転送

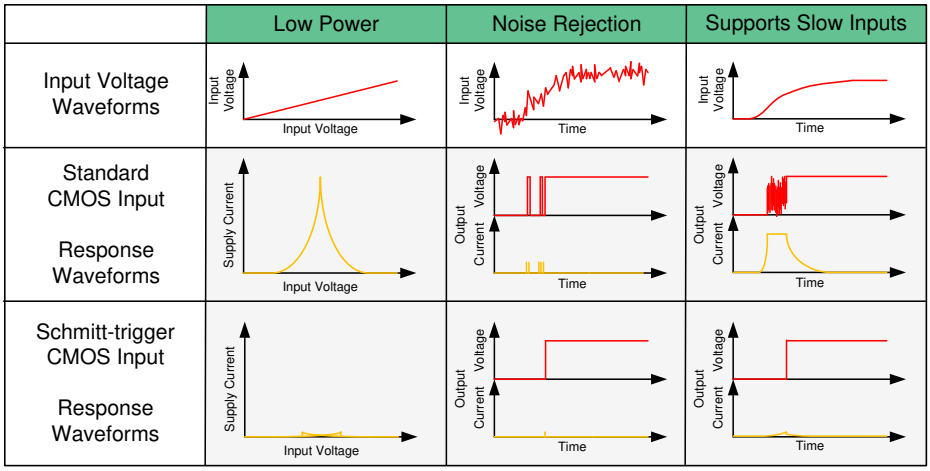
3 概要

SN74HCS138 は、1 つの通常の出力ストローブ (G_2) と 2 つのアクティブ LOW 出力ストローブ ($\overline{G}_1$、$\overline{G}_0$) を備えた 3 - 8 デコーダです。いずれかのストローブ入力により出力が無効化されると、すべての出力は HIGH 状態に強制されます。ストローブ入力により出力が無効化されている場合以外は、選択された出力のみが LOW であり、その他のすべての出力は HIGH です。

デバイス情報

部品番号	パッケージ (1)	本体サイズ (公称)
SN74HCS138PW	TSSOP (16)	5.00mm × 4.40mm
SN74HCS138D	SOIC (16)	9.90mm × 3.90mm
SN74HCS138BQB	WQFN (16)	3.50mm × 2.50mm
SN74HCS138DYY	SOT-23-THN (16)	4.20mm × 2.00mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



シュミット・トリガ入力の利点

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4 Revision History

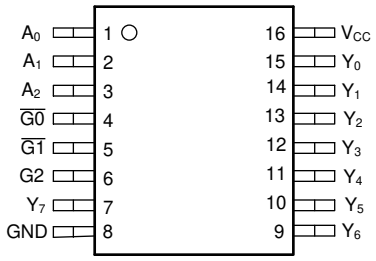
資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (September 2020) to Revision A (November 2020)	Page
• 「デバイス情報」表に BQB パッケージを追加	1
• Added BQB Package pinout diagram	3
• Added BQB Package to *Thermal Information* table	5

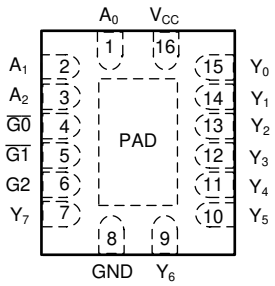
Changes from Revision A (October 2020) to Revision B (May 2021)	Page
• 「デバイス情報」表に DYY パッケージを追加	1
• Added DYY Package pinout diagram and information to *Pin Configuration and Functions*	3
• Added DYY Package to *Thermal Information* table	5

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5 Pin Configuration and Functions



D, PW, or DYY Package
16-Pin SOIC, TSSOP, or SOT-23
Top View



BQB Package
16-Pin WQFN
Top View

表 5-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
A_0	1	I	Address select 0
A_1	2	I	Address select 1
A_2	3	I	Address select 2
$\overline{G}_0$	4	I	Strobe input, active low
$\overline{G}_1$	5	I	Strobe input, active low
G_2	6	I	Strobe input
Y_7	7	O	Output 7
GND	8	—	Ground
Y_6	9	O	Output 6
Y_5	10	O	Output 5
Y_4	11	O	Output 4
Y_3	12	O	Output 3
Y_2	13	O	Output 2
Y_1	14	O	Output 1
Y_0	15	O	Output 0
V_{CC}	16	—	Positive supply
Thermal Pad(1)		—	The thermal pad can be connect to GND or left floating. Do not connect to any other signal or supply.

(1) BQB package only.

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	7	V
I_{IK}	Input clamp current(2)	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V		±20	mA
I_{OK}	Output clamp current(2)	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V		±20	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±35	mA
	Continuous current through V_{CC} or GND			±70	mA
T_J	Junction temperature(3)			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
(3) Guaranteed by design.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±4000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	2	5	6	V
V_I	Input voltage	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	V
T_A	Ambient temperature	–40		125	°C

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6.4 Thermal Information

THERMAL METRIC[1]		SN74HCS138				UNIT
		PW (TSSOP)	D (SOIC)	BQB (WQFN)	DYY (SOT)	
		16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	141.2	122.2	108.4	186.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	78.8	80.9	77.3	109.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	85.8	80.6	74.4	111.0	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	27.7	40.4	12.6	18.0	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	85.5	80.3	74.5	110.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	54.3	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP	MAX	UNIT
V_{T+}	Positive switching threshold			2 V	0.7		1.5	V
				4.5 V	1.7		3.15	
				6 V	2.1		4.2	
V_{T-}	Negative switching threshold			2 V	0.3		1.0	V
				4.5 V	0.9		2.2	
				6 V	1.2		3.0	
ΔV_T	Hysteresis (V_{T+} - V_{T-})[1]			2 V	0.2		1.0	V
				4.5 V	0.4		1.4	
				6 V	0.6		1.6	
V_{OH}	High-level output voltage	V_I = V_{IH} or V_{IL}	I_{OH} = -20 µA	2 V to 6 V	V_{CC} – 0.1	V_{CC} – 0.002		V
			I_{OH} = -6 mA	4.5 V	4.0	4.3		
			I_{OH} = -7.8 mA	6 V	5.4	5.75		
V_{OL}	Low-level output voltage	V_I = V_{IH} or V_{IL}	I_{OL} = 20 µA	2 V to 6 V		0.002	0.1	V
			I_{OL} = 6 mA	4.5 V		0.18	0.30	
			I_{OL} = 7.8 mA	6 V		0.22	0.33	
I_I	Input leakage current	V_I = V_{CC} or 0		6 V		±100	±1000	nA
I_{CC}	Supply current	V_I = V_{CC} or 0, I_O = 0		6 V		0.1	2	µA
C_i	Input capacitance			2 V to 6 V			5	pF

(1) Guaranteed by design.

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6.6 Switching Characteristics

C_L = 50 pF; over operating free-air temperature range (unless otherwise noted). See Parameter Measurement Information.

PARAMETER		FROM	TO	V_{CC}	Operating free-air temperature (T_A)						UNIT
					25°C			–40°C to 125°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
t_{pd}	Propagation delay	A, B, or C	Any Y	2 V		21	33			53	ns
				4.5 V		8	12			19	
				6 V		7	11			16	
		G	Any Y	2 V		22	33			54	
				4.5 V		8	12			19	
				6 V		7	11			16	
t_t	Transition-time		Any output	2 V			9			17	ns
				4.5 V			5			8	
				6 V			4			7	

6.7 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS	V_{CC}	MIN	TYP	MAX	UNIT
C_{pd}	Power dissipation capacitance per gate	No load	2 V to 6 V		40		pF

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6.8 Typical Characteristics

T_A = 25°C

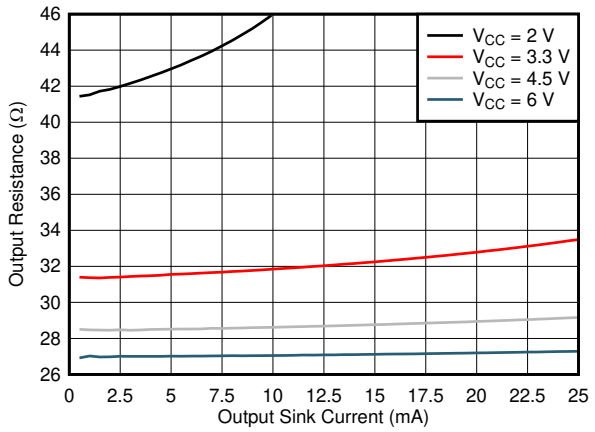


図 6-1. Output driver resistance in LOW state.

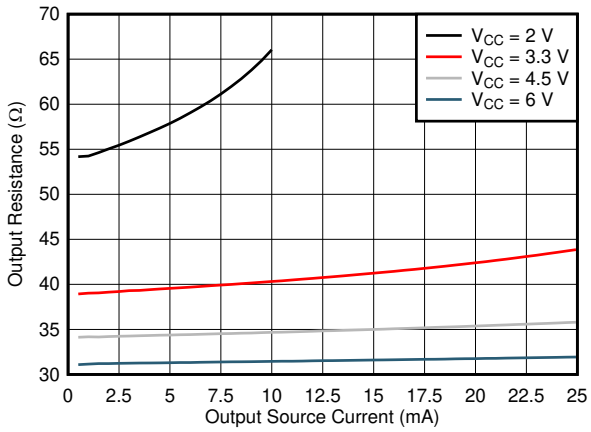


図 6-2. Output driver resistance in HIGH state.

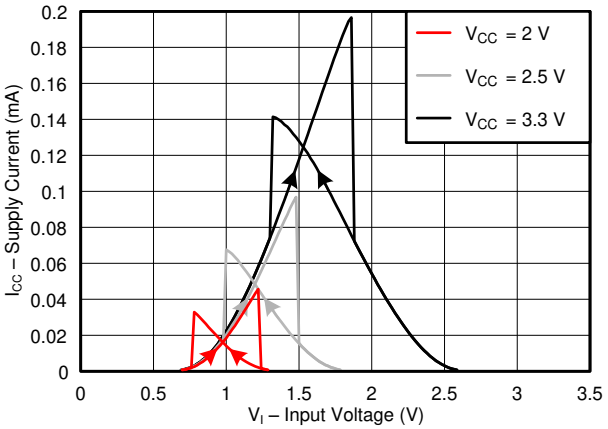


図 6-3. Supply current across input voltage, 2-, 2.5-, and 3.3-V supply

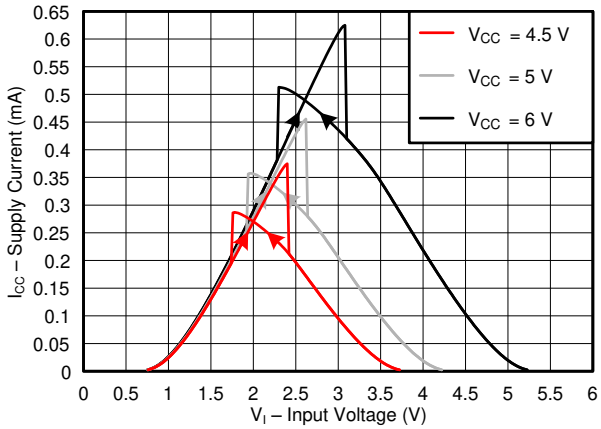


図 6-4. Supply current across input voltage, 4.5-, 5-, and 6-V supply

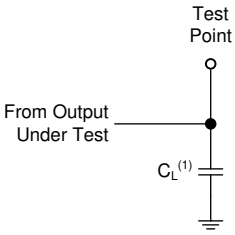
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7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_t < 2.5 ns.

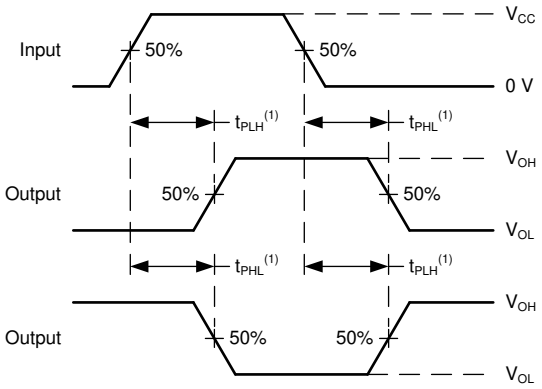
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



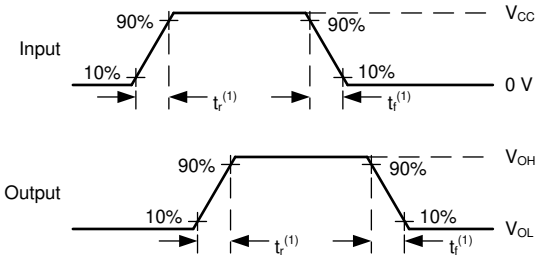
(1) C_L includes probe and test-fixture capacitance.

図 7-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

図 7-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

図 7-3. Voltage Waveforms, Input and Output Transition Times

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8 Detailed Description

8.1 Overview

The SN74HCS138 is a high speed silicon gate CMOS decoder well suited to memory address decoding or data routing applications. It contains a single 3:8 decoder. All inputs include Schmitt-triggers allowing for slow input transitions and providing additional noise margin.

The SN74HCS138 has three address select inputs (A_2, A_1, and A_0). The circuit functions as a normal one-of-eight decoder.

Three strobe inputs ($\overline{G}_2$, $\overline{G}_1$ and G_0) are provided to simplify cascading and to facilitate demultiplexing. When any input strobe is active, all outputs are forced into the high state.

The demultiplexing function is accomplished by first using the select inputs to choose the desired output, and then using one of the strobe inputs as the data input.

The outputs for the SN74HCS138 are normally high, and low when selected.

8.2 Functional Block Diagram

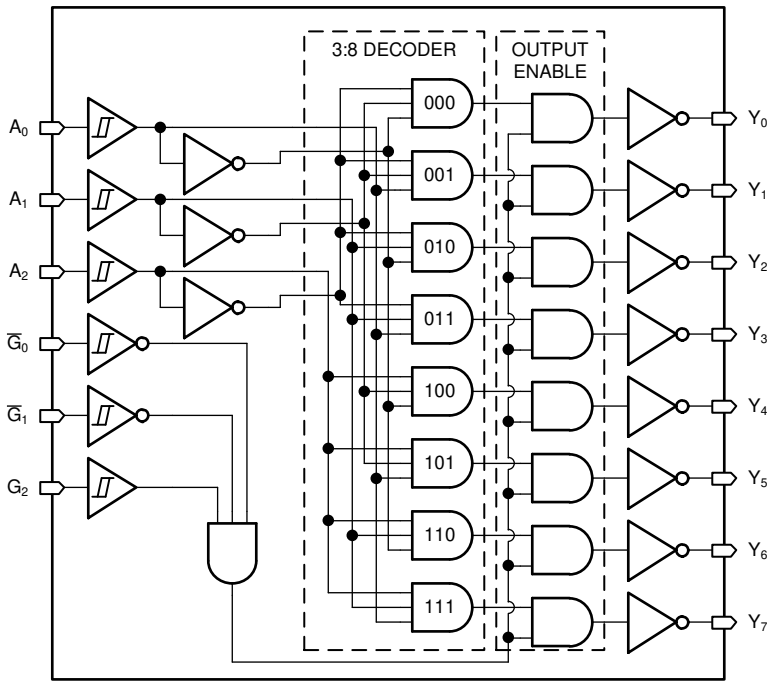


図 8-1. Logic Diagram (Positive Logic) for the SN74HCS138

8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

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8.3.2 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law (R = V ÷ I).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Electrical Placement of Clamping Diodes for Each Input and Output.

> **注意**
>
> Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

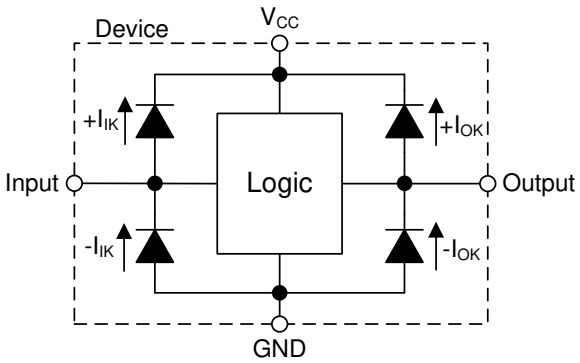


図 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

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8.4 Device Functional Modes

Function Table lists the functional modes of the SN74HCS138.

表 8-1. Function Table

INPUTS(1)						OUTPUTS							
G_2	$\overline{G}_1$	$\overline{G}_0$	A_2	A_1	A_0	Y_0	Y_1	Y_2	Y_3	Y_4	Y_5	Y_6	Y_7
X	X	H	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
X	H	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	L	H	H	H	H
H	L	L	H	L	L	H	H	H	H	L	H	H	H
H	L	L	H	L	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care

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9 Application and Implementation

注

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9.1 Application Information

The SN74HCS138 is used to control multiple devices that operate on a shared data bus. A decoder provides the capability to have a binary encoded input activate only one of the device's outputs. This is ideal for solid state memory applications where multiple devices have to be read or written to with a limited number of GPIO pins used on the system controller. The decoder is used to activate the chip select (CS) input to the selected memory device, and the controller can then read or write from that device alone when using a shared bus.

9.2 Typical Application

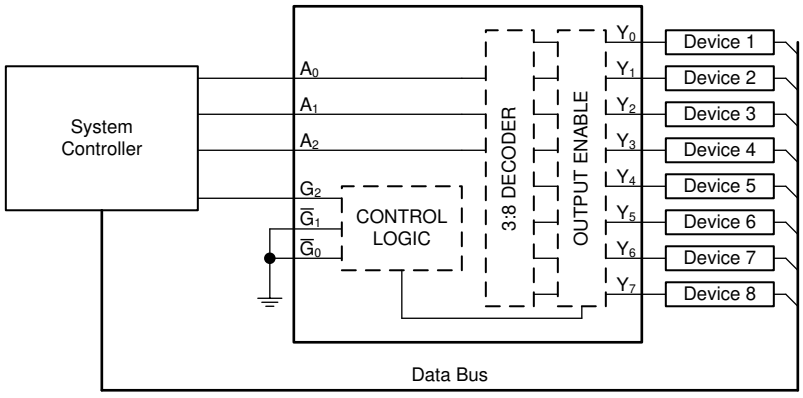


図 9-1. Typical application block diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS138 plus the maximum static supply current, I_{CC}, listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS138 plus the maximum supply current, I_{CC}, listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCS138 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HCS138 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL}. When outputting in the high state, the

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output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and Cpd Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

> **注意**
>
> The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS138, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-kΩ resistor value is often used due to these factors.

The SN74HCS138 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.

2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS138 to the receiving device(s).
3. Ensure the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation.

9.2.3 Application Curve

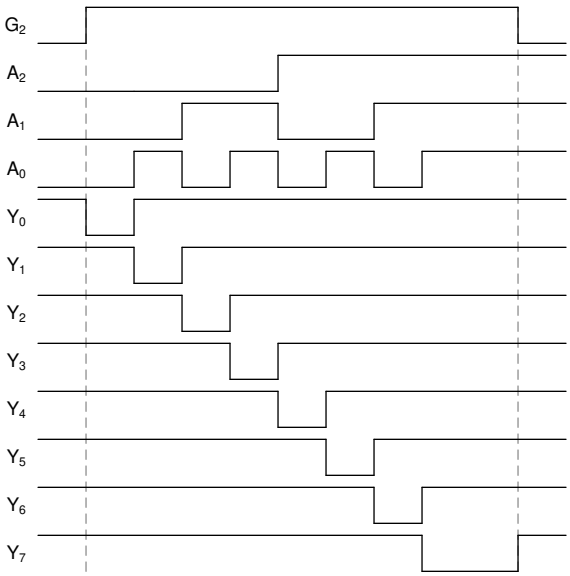


図 9-2. Application timing diagram

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10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

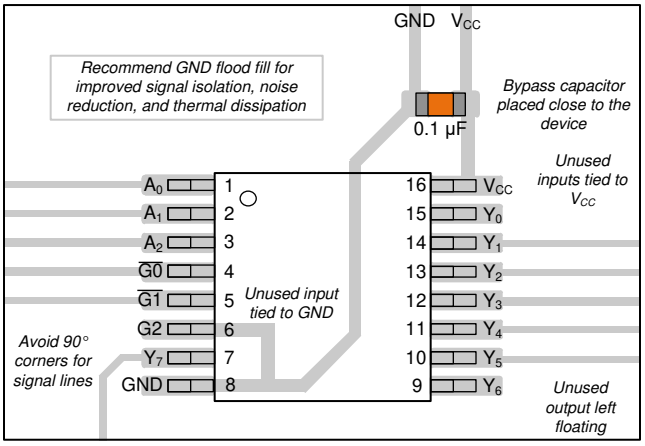


図 11-1. Example layout for the SN74HCS138.

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *HCMOS Design Considerations* application report (SCLA007)
- Texas Instruments, *CMOS Power Consumption and C_{pd} Calculation* application report (SDYA009)
- Texas Instruments, *Designing With Logic* application report

12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.com のデバイス製品フォルダを開いてください。*「更新の通知を受け取る」をクリック*して登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.3 サポート・リソース

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12.5 静電気放電に関する注意事項

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ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

12.6 用語集

TI 用語集　この用語集には、用語や略語の一覧および定義が記載されています。

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13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74HCS138BQBR	Active	Production	WQFN (BQB) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS138
SN74HCS138BQBR.A	Active	Production	WQFN (BQB) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS138
SN74HCS138DR	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	HCS138
SN74HCS138DR.A	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS138
SN74HCS138DYYR	Active	Production	SOT-23-THIN (DYY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS138
SN74HCS138DYYR.A	Active	Production	SOT-23-THIN (DYY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS138
SN74HCS138PWR	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	HCS138
SN74HCS138PWR.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS138

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74HCS138 :

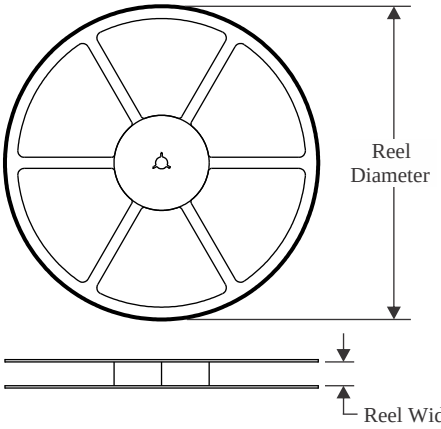
- Automotive : SN74HCS138-Q1

NOTE: Qualified Version Definitions:

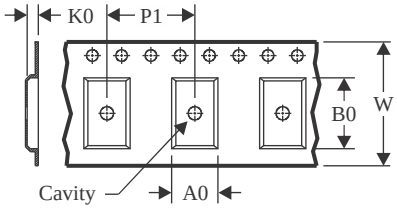
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

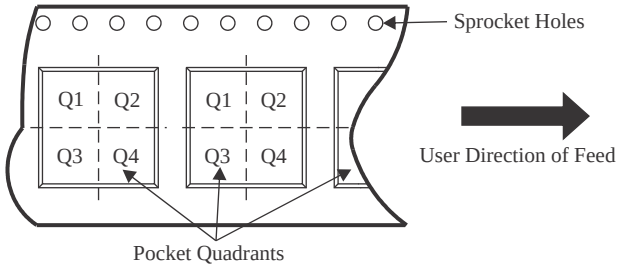


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

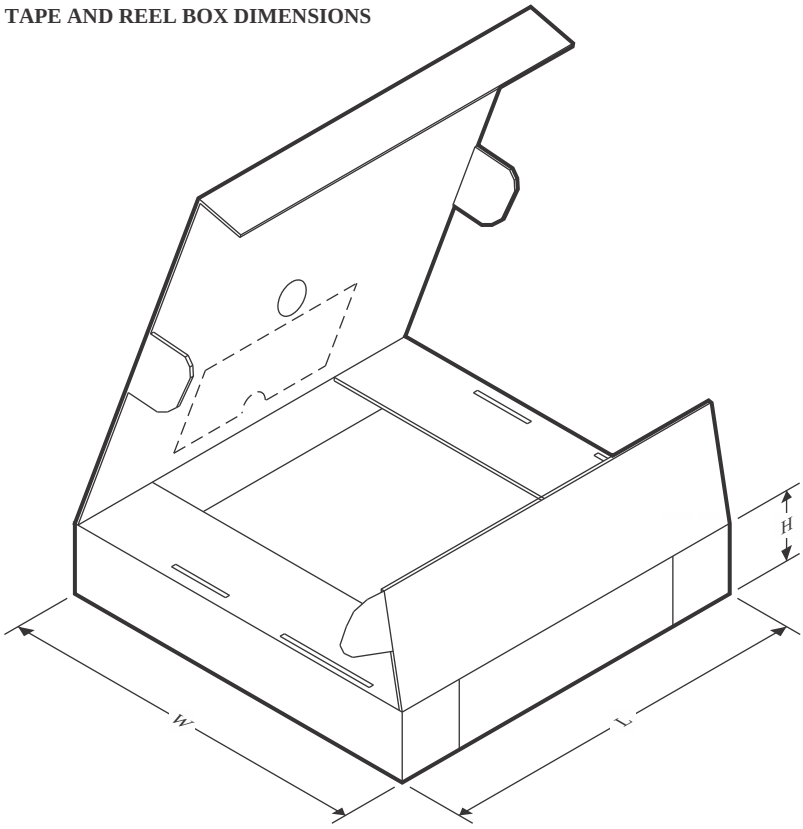
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS138BQBR	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1
SN74HCS138DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74HCS138DYYR	SOT-23-THIN	DYY	16	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
SN74HCS138PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.3	1.6	8.0	12.0	Q1
SN74HCS138PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

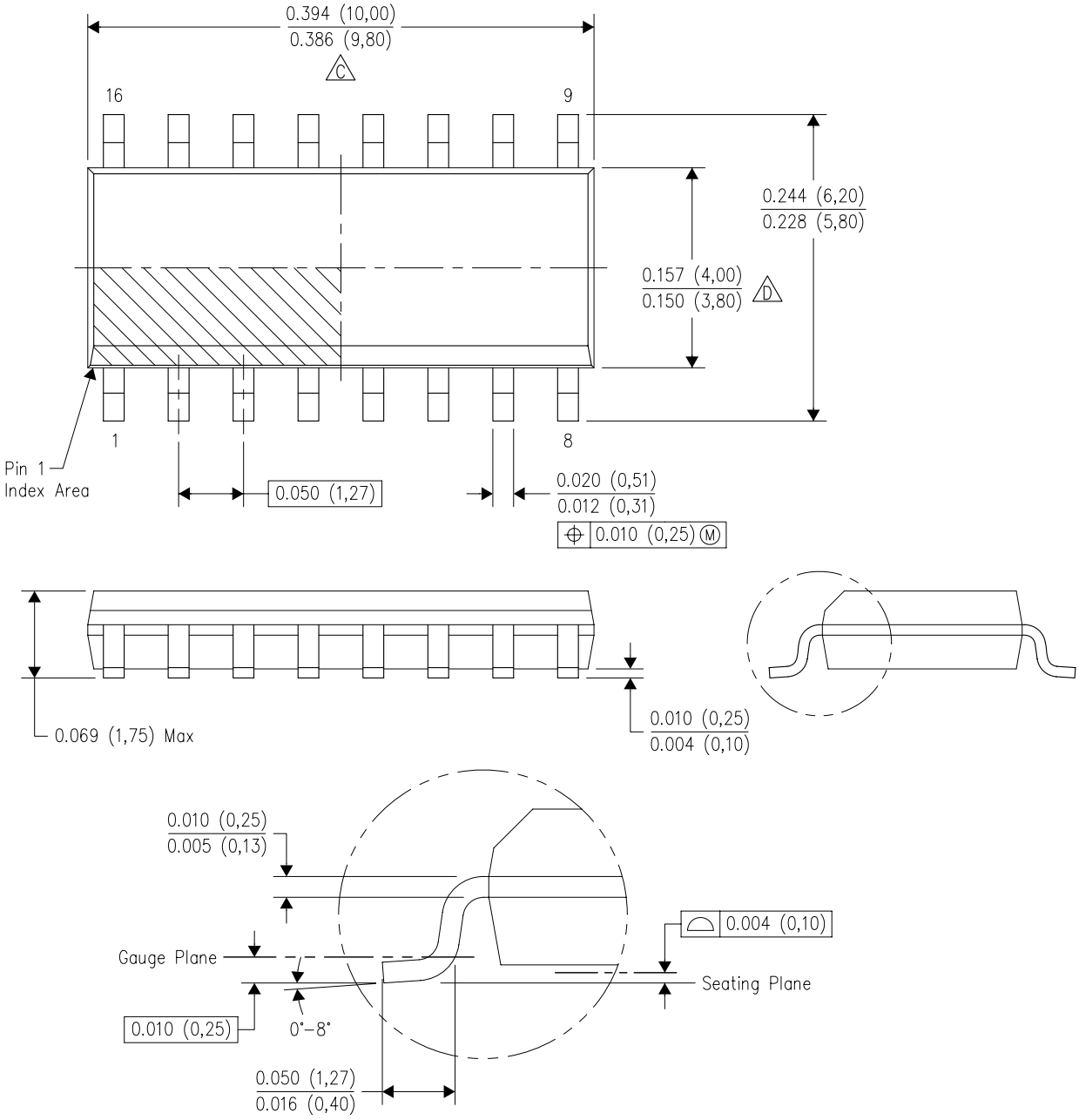
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS138BQBR	WQFN	BQB	16	3000	210.0	185.0	35.0
SN74HCS138DR	SOIC	D	16	2500	353.0	353.0	32.0
SN74HCS138DYYR	SOT-23-THIN	DYY	16	3000	336.6	336.6	31.8
SN74HCS138PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74HCS138PWR	TSSOP	PW	16	2000	356.0	356.0	35.0

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

GENERIC PACKAGE VIEW

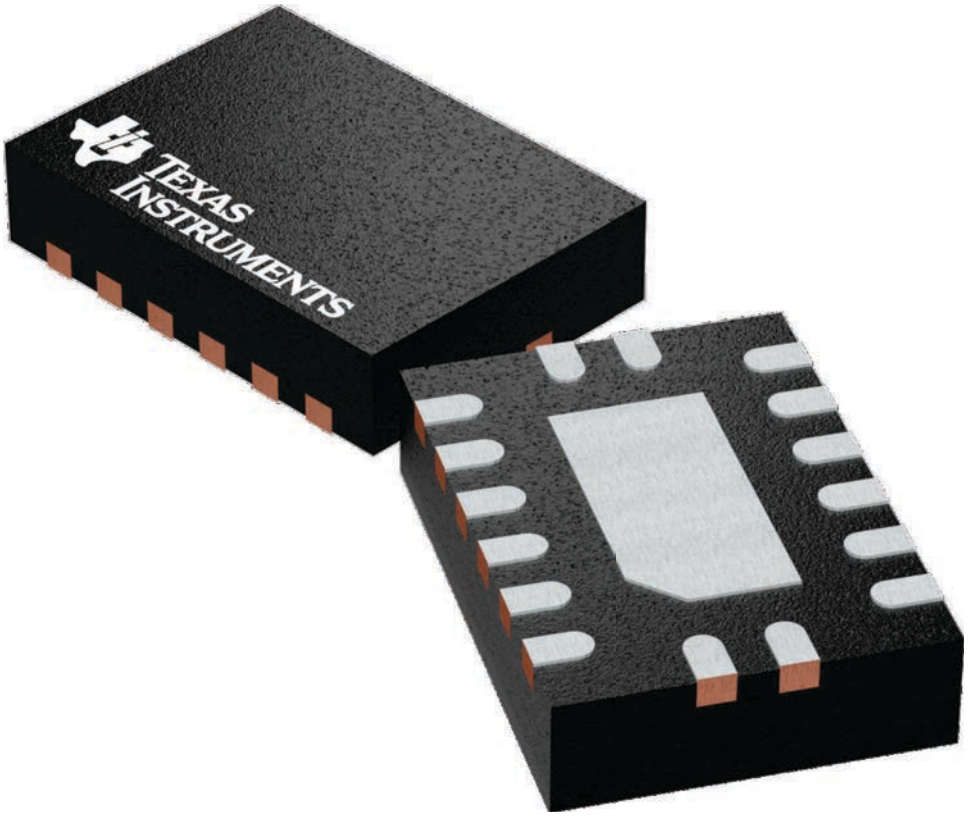
BQB 16

WQFN - 0.8 mm max height

2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



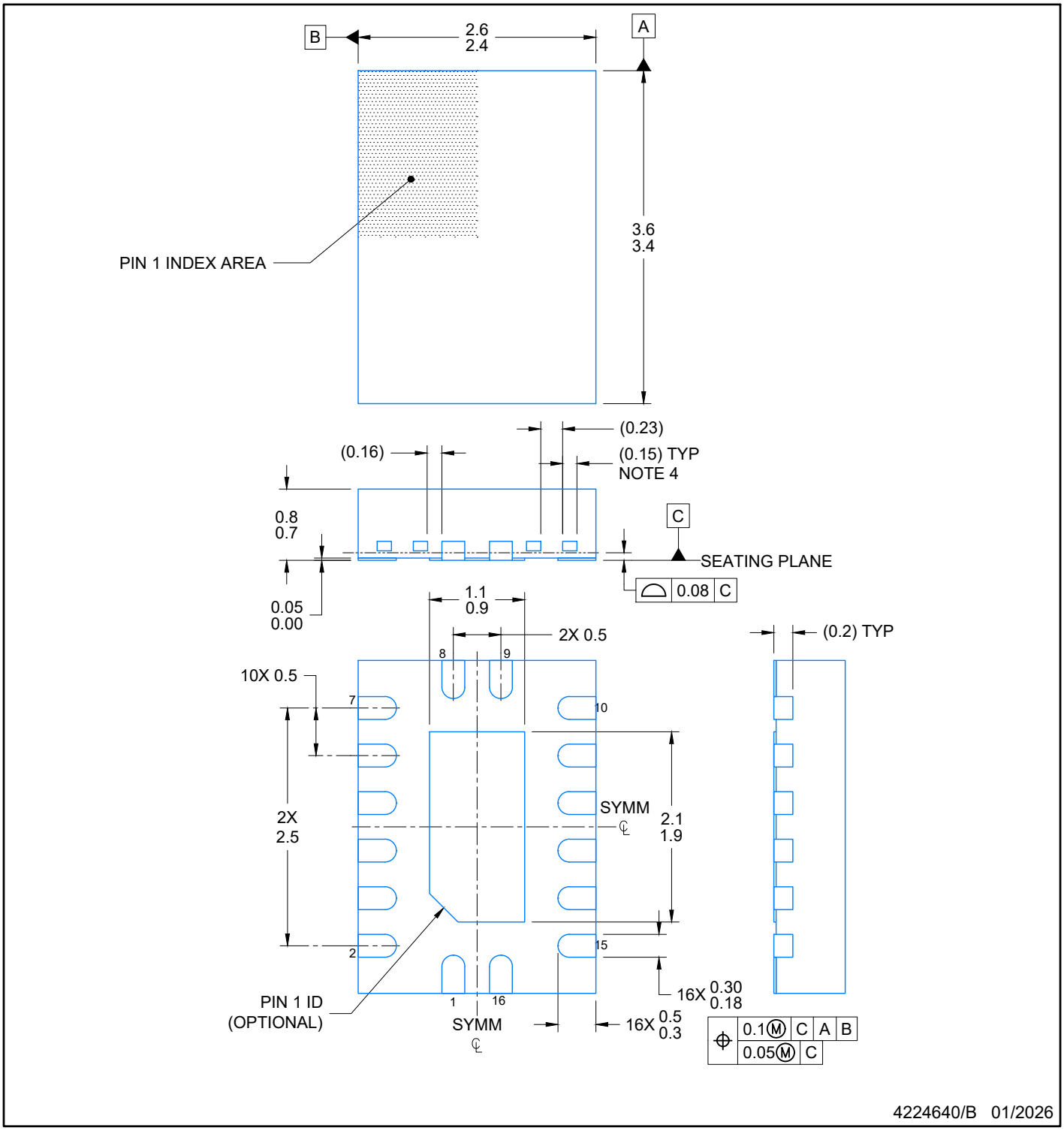
4226161/A

PACKAGE OUTLINE

BQB0016A

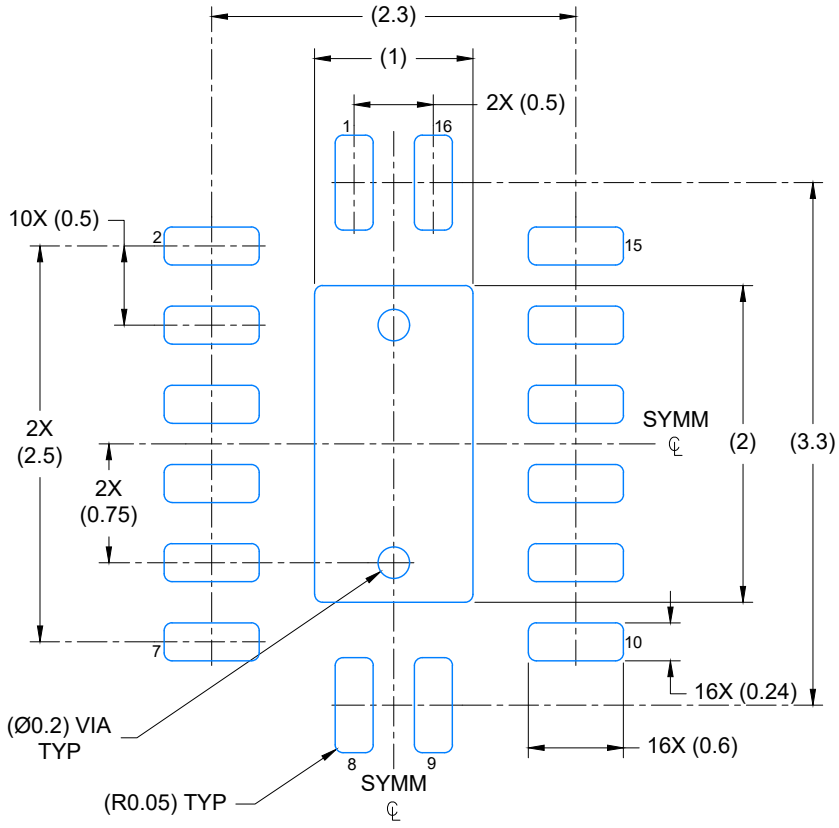
WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD

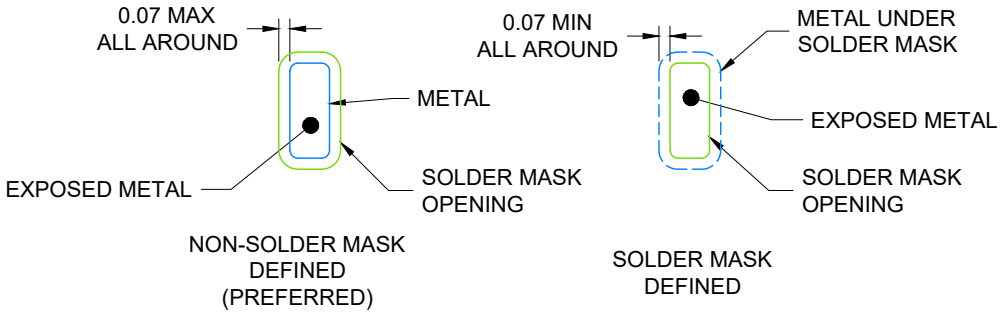


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.
4. Features may differ or may not be present



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

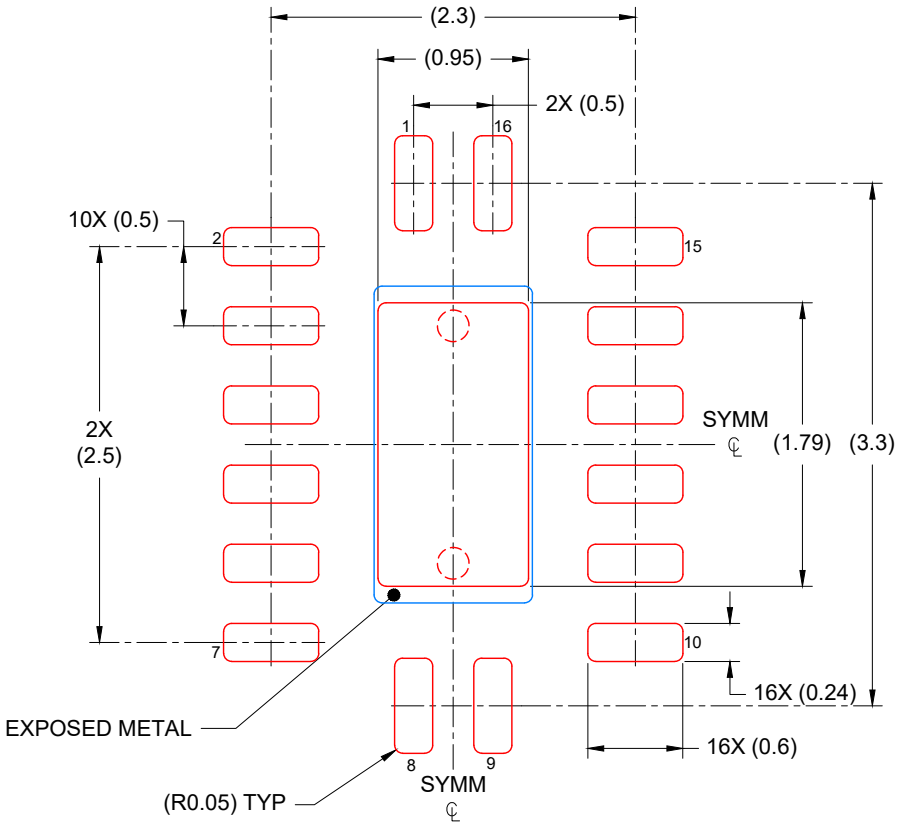


4224640/B 01/2026

1. NOTES: (continued)

5. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

6. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
85% PRINTED COVERAGE BY AREA
SCALE: 20X

4224640/B 01/2026

NOTES: (continued)

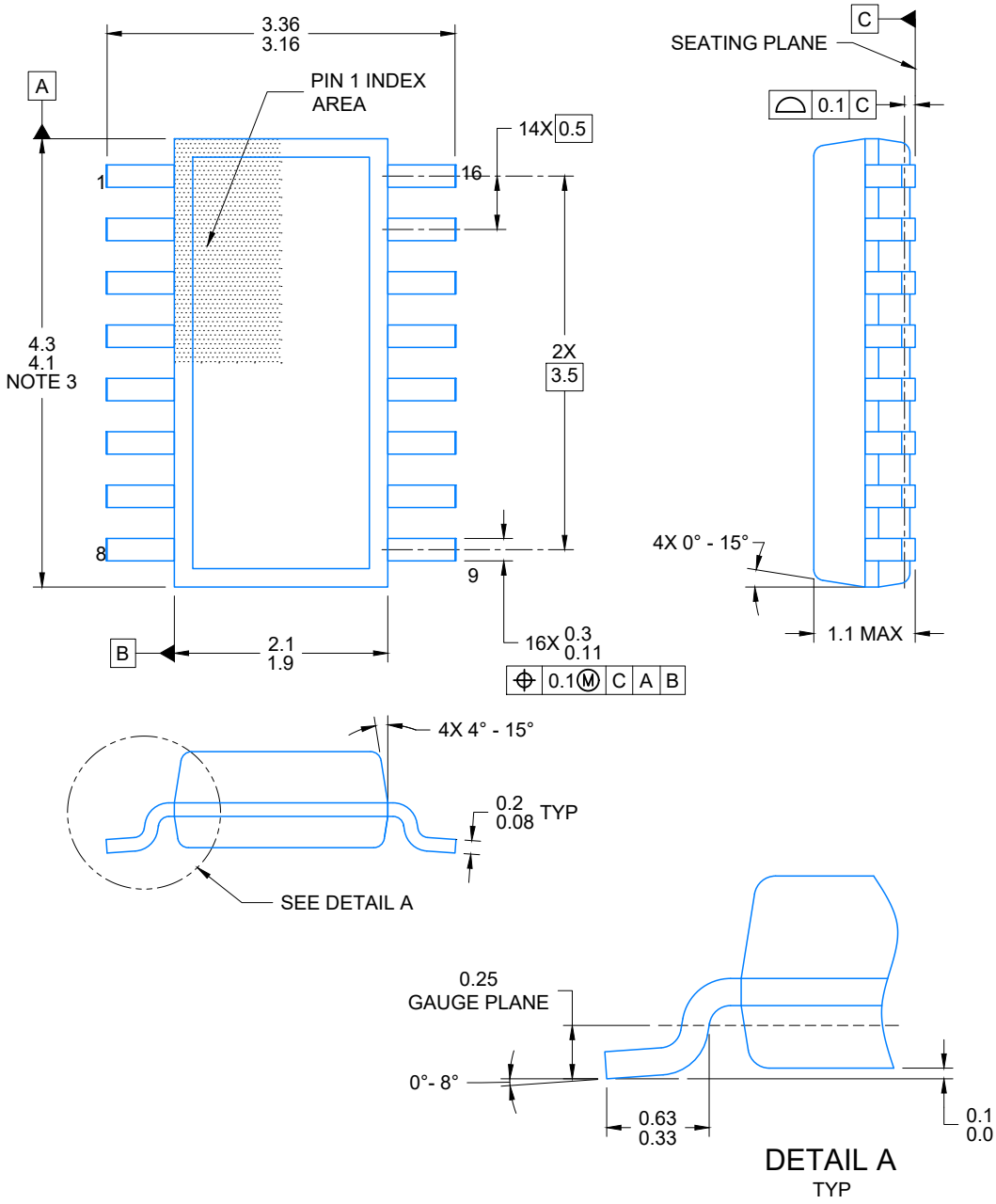
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE

DYY0016A

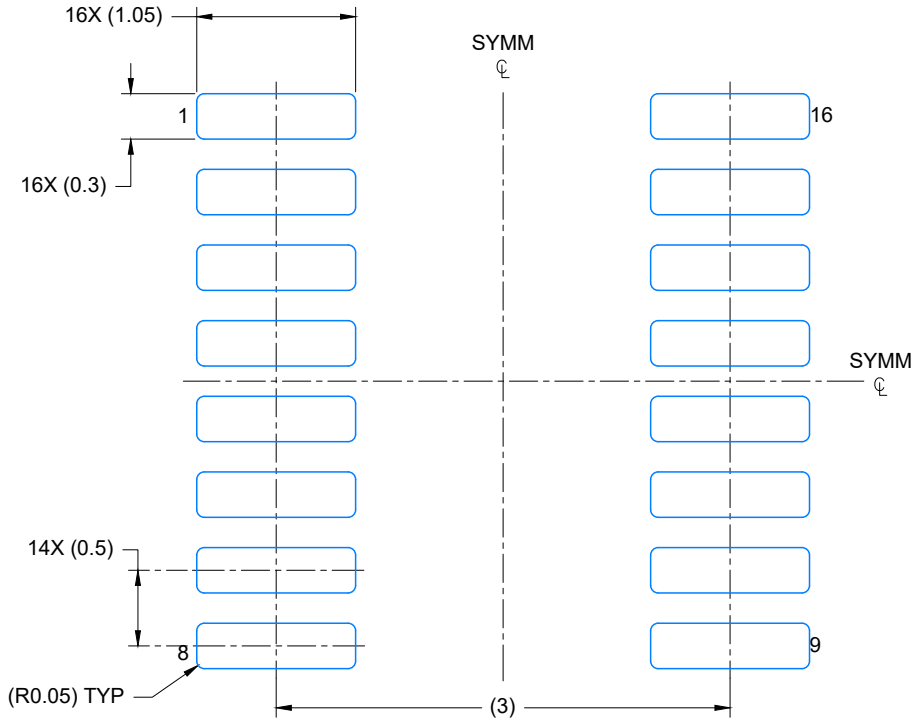
SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE

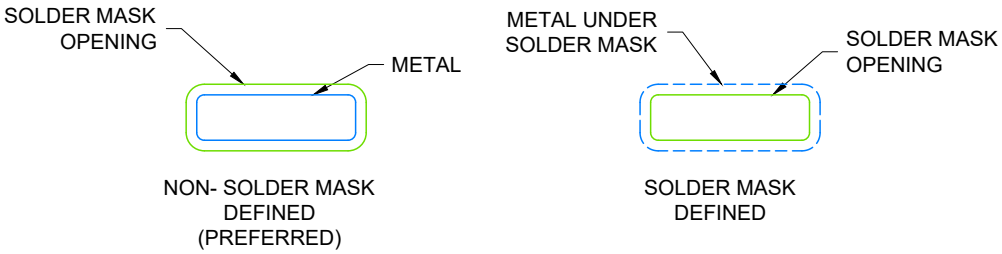


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AA



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



SOLDER MASK DETAILS

4224642/D 07/2024

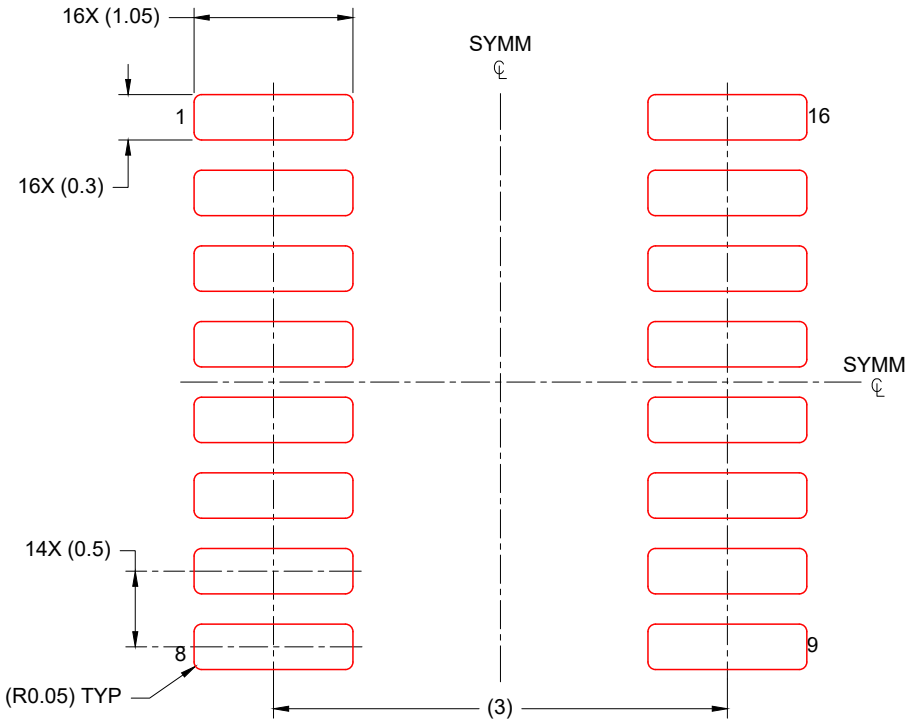
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 20X

4224642/D 07/2024

NOTES: (continued)

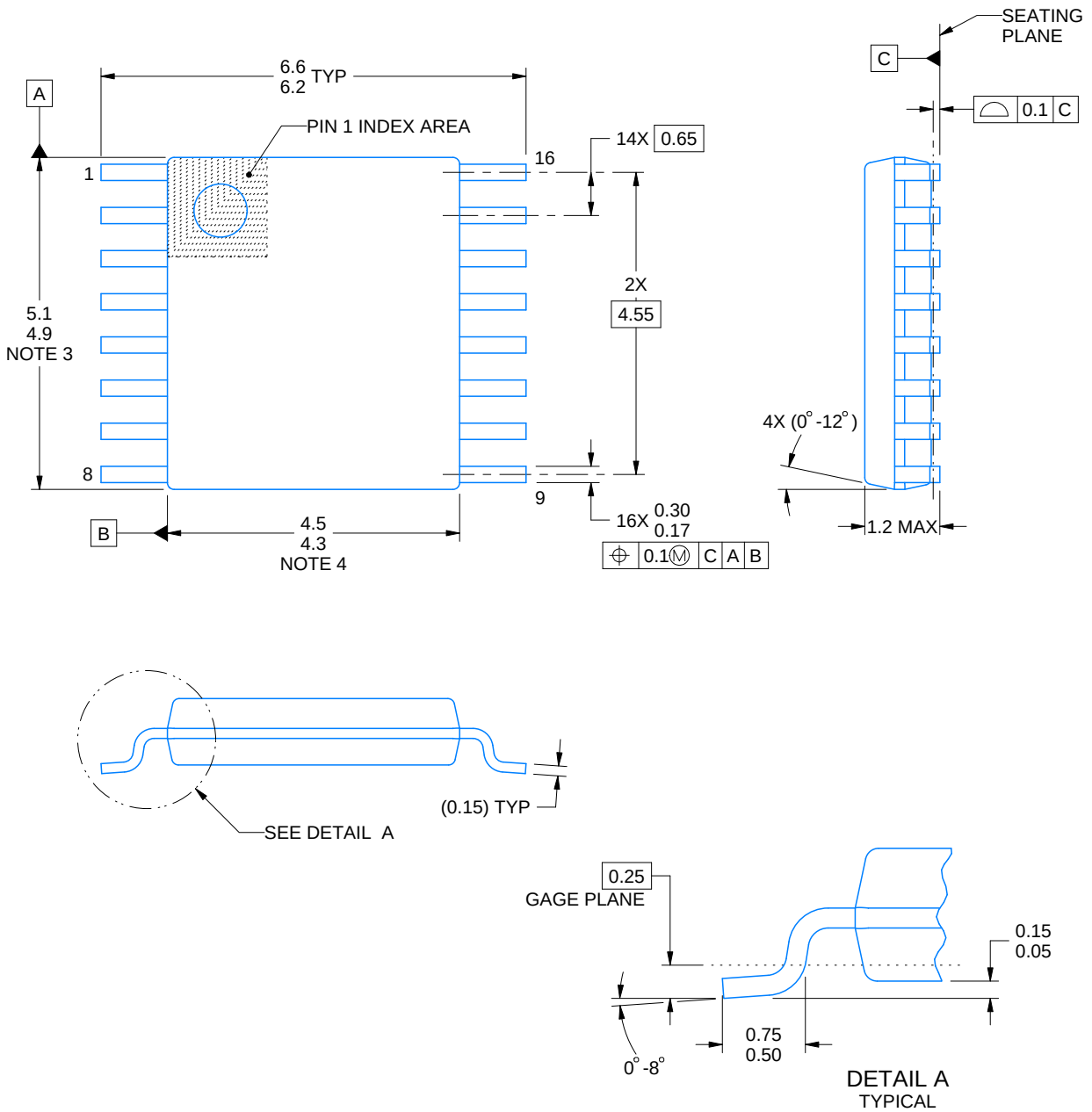
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

PW0016A

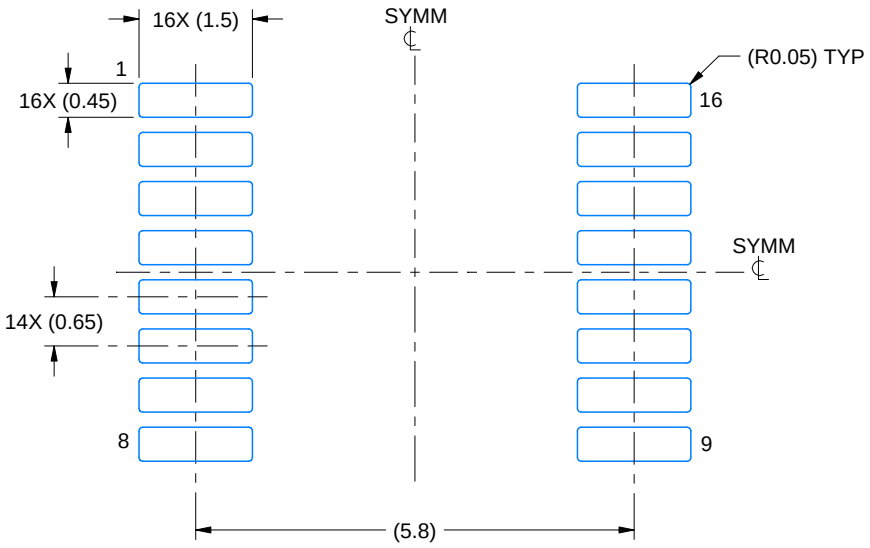
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

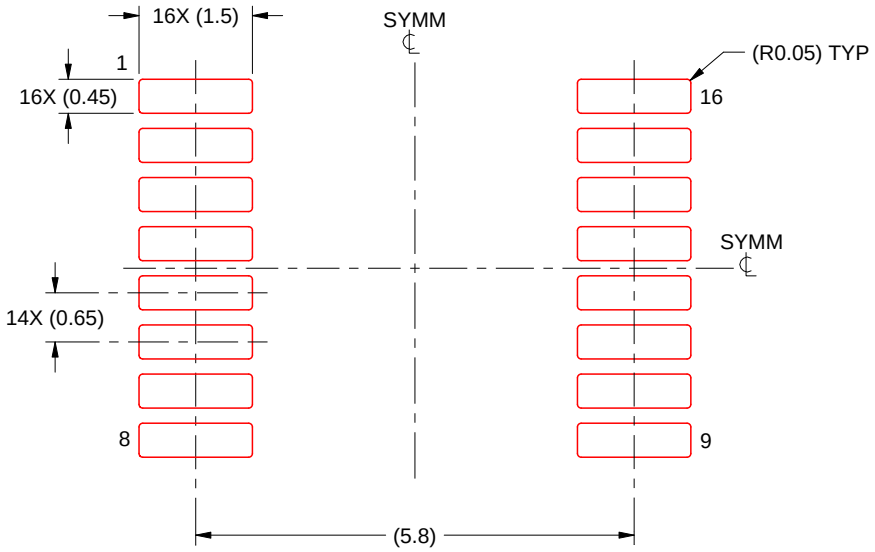


SOLDER MASK DETAILS

4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要なお知らせと免責事項

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